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Substitute for form 1449A/B/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use as many sheets as necessary)

Sheet 1 of 1

Complete if Known	
Application Number	Unassigned
Filing Date	January 28, 2004
First Named Inventor	Yutaka ARIMA
Group Art Unit	Unassigned
Examiner Name	Unassigned
Attorney Docket Number	402952/SAKAI

U.S. PATENT DOCUMENTS

Examiner Initials	Doc. No.	U.S. Patent Document: Application or Patent Number	U.S. Patent Document: Kind Code	Name of Patentee or Applicant	Date of Publication	Filing Date If Appropriate
SW	A1	2003/0030081		Arima	2/13/2003	

FOREIGN PATENT DOCUMENTS

Examiner Initials	Doc. No.	Foreign Patent Document: Office	Foreign Patent Document: Application or Patent Number	Foreign Patent Document: Kind Code	Name of Patentee or Applicant	Date of Publication	Translation: Yes	Translation: No*+
SW	A2	JP	2002-222944 A		K.K. KITAKYUSYU TECHNOLOGY CENTER	8/9/2002		X+

OTHER - NON PATENT LITERATURE DOCUMENTS

Examiner Initials	Doc. No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number (s), publisher, city and/or country where published.	Translation: Yes	Translation: No*+
SW	A3	T. SHIBATA et al., "A Functional MOS Transistor Featuring Gate-Level Weighted Sum and Threshold Operations" *IEEE Transactions on Electron Devices, June 1992, pp. 1444-1455, Vol. 39(6)*		
SW	A4	T. HASHIMOTO et al., "Thin Film Effects of Double-Gate Polysilicon MOSFET," *Extended Abstracts of the 22nd (1990 International) Conference on Solid State Devices and Materials, Sendai, 1990, pp. 393-396, JAPAN*		
SW	A5	T. HIRAMOTO et al., "Low Power and Low Voltage MOSFETs with Variable Threshold Voltage Controlled by Back-Bias," *IEICE Trans. Electron, February 2000, pp. 161-169, Vol. E84-C(2).*		

Examiner Signature		Date Considered	9-9-2004

* A concise statement of relevance is being submitted in lieu of a translation. 37 CFR 1.98(a)(3).

\+ An English-language equivalent/patent, or an English-language abstract, or an English-language version of the search report or action by a foreign patent office in a counterpart foreign application indicating the degree of relevance found by the foreign office is being submitted in lieu of a concise explanation of relevance under 37 CFR 1.98(a)(3).